

100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	Max R _{DS(on)}	Max I _D T _A = 25°C (Note 5)
100V	250mΩ @ V _{GS} = 10V	1.9A
	300mΩ @ V _{GS} = 6V	1.68A

Description and Applications

This MOSFET features a unique structure, combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency, power management applications.

- DC - DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

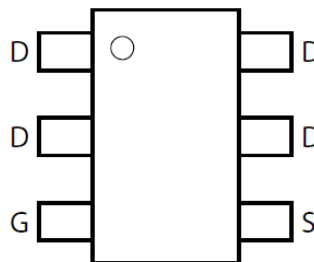
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

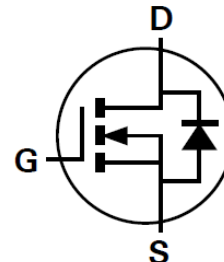
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓜ3
- Weight: 0.015 grams (Approximate)



Top View



Pinout Top-view



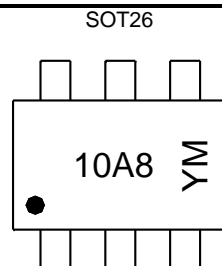
Device symbol

Ordering Information (Note 4)

Part Number	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMN10A08E6TA	7	8	3000
ZXMN10A08E6TC	13	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



10A8 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: C = 2015)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	C	D	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

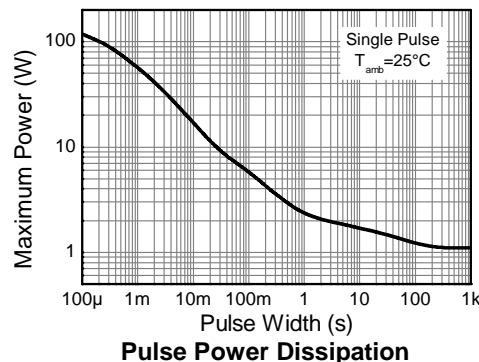
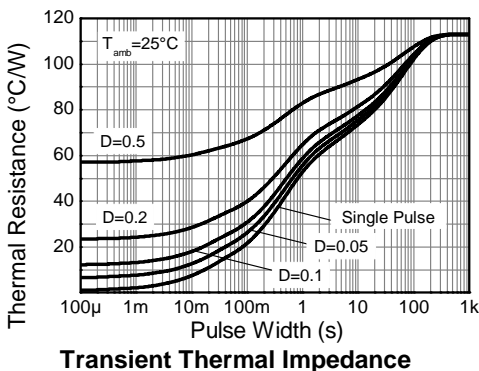
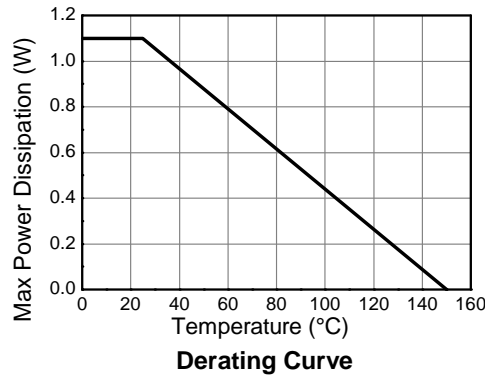
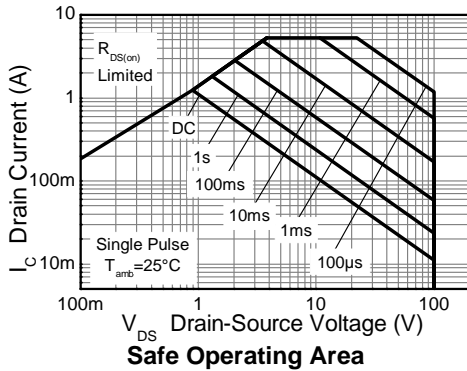
Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	100	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current	V _{GS} = 10V	I _D	Note 5)	1.9	A
			T _A =+70°C (Note 5)	1.5	
			(Note 4)	1.5	
			(Note 7)	3.5	
Pulsed Drain Current		I _{DM}	8.6	A	
Continuous Source Current (Body Diode)		I _S	2.5	A	
Pulsed Source Current (Body Diode)		I _{SM}	8.6	A	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	P _D	1.1	W
	(Note 5)		1.7	
	(Note 7)		6.3	
Thermal Resistance, Junction to Ambient	(Note 4)	R _{θJA}	114	°C/W
	(Note 5)		73.5	
Thermal Resistance, Junction to Leads	(Note 7)	R _{θJL}	19.7	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes:
4. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 5. For a device surface mounted on FR4 PCB measured at t ≤ 5 sec.
 6. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300µs - pulse width limited by maximum junction temperature.
 7. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

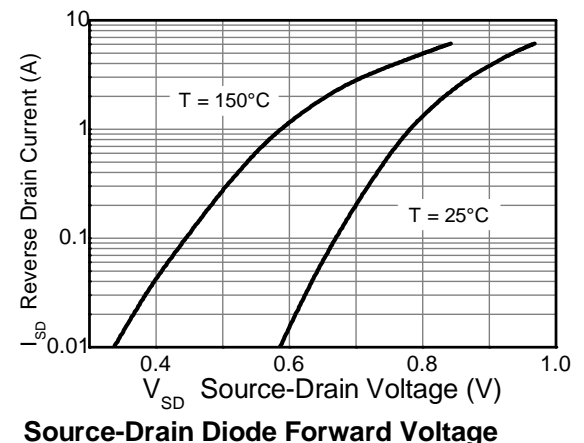
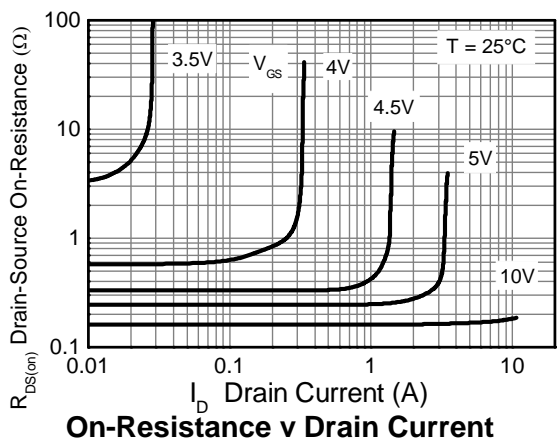
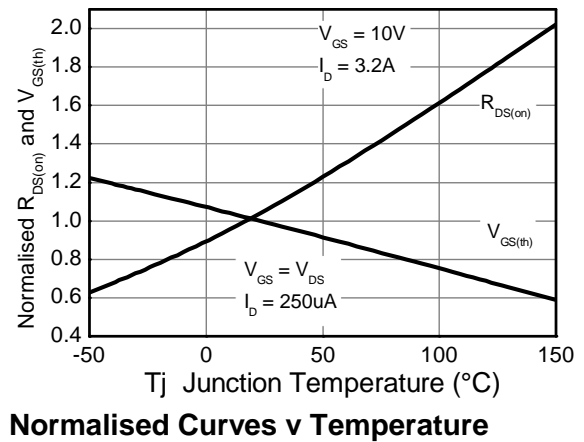
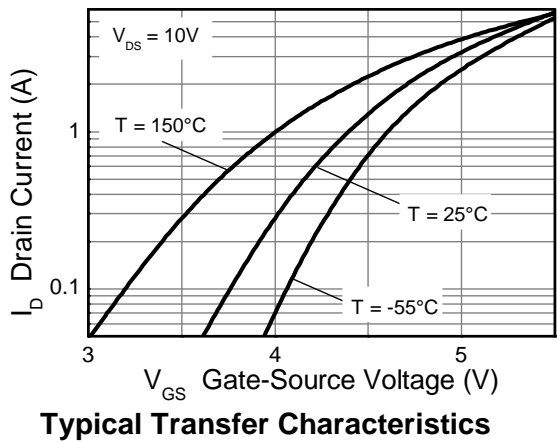
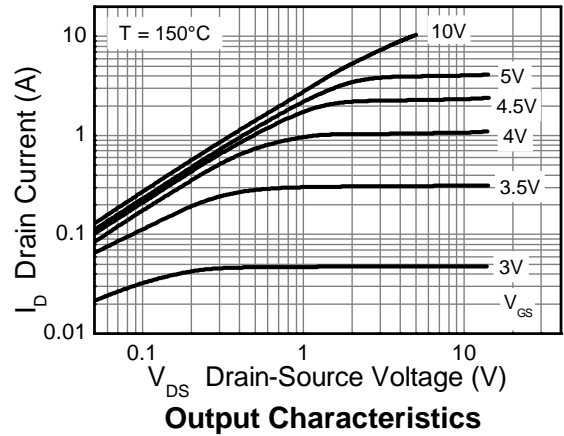
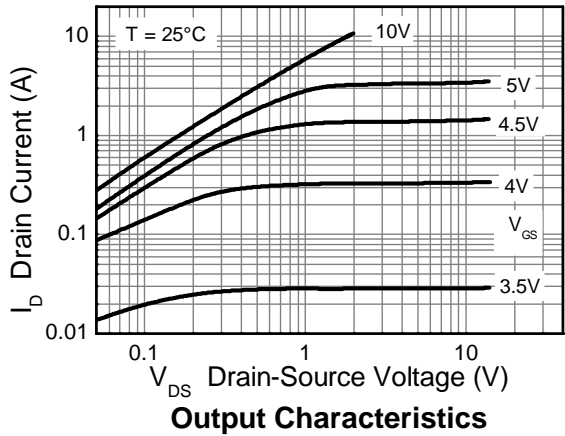


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

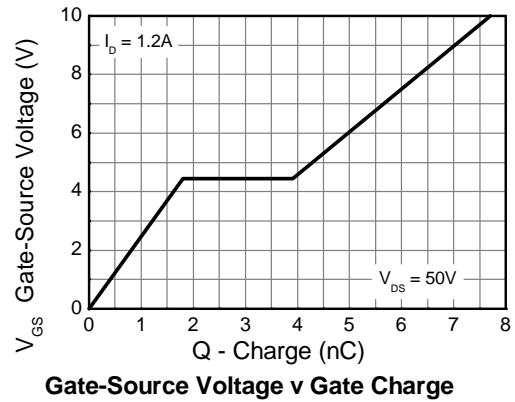
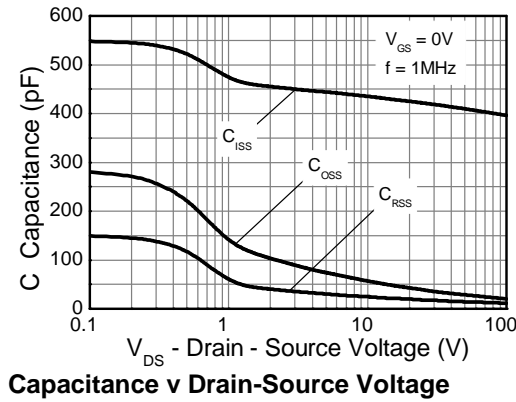
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	I _D = 250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	2.0	—	4.0	V	I _D = 250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 8)	R _{DS(on)}	—	—	0.25	Ω	V _{GS} = 10V, I _D = 3.2A
				0.30		V _{GS} = 6V, I _D = 2.6A
Forward Transconductance (Notes 8 & 10)	g _{fs}	—	5.0	—	S	V _{DS} = 15V, I _D = 3.2A
Diode Forward Voltage (Note 8)	V _{SD}	—	0.87	0.95	V	I _S = 3.2A, V _{GS} = 0V
Reverse Recovery Time (Note 10)	t _{rr}	—	27	—	ns	I _S = 1.2A, di/dt = 100A/μs
Reverse Recovery Charge (Note 10)	Q _{rr}	—	32	—	nC	
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	405	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	28.2	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	14.2	—	pF	
Gate Charge (Note 9)	Q _g	—	4.2	—	nC	V _{GS} = 5V, V _{DS} = 50V I _D = 1.2A
Total Gate Charge (Note 9)	Q _g	—	7.7	—	nC	V _{GS} = 10V, V _{DS} = 50V I _D = 1.2A
Gate-Source Charge (Note 9)	Q _{gs}	—	1.8	—	nC	
Gate-Drain Charge (Note 9)	Q _{gd}	—	2.1	—	nC	
Turn-On Delay Time (Note 9)	t _{d(on)}	—	3.4	—	ns	V _{DD} = 30V, V _{GS} = 10V I _D = 1.2A, R _G ≅ 6.0Ω
Turn-On Rise Time (Note 9)	t _r	—	2.2	—	ns	
Turn-Off Delay Time (Note 9)	t _{d(off)}	—	8	—	ns	
Turn-Off Fall Time (Note 9)	t _f	—	3.2	—	ns	

- Notes:
8. Measured under pulsed conditions. Width ≤300μs. Duty cycle ≤2%.
 9. Switching characteristics are independent of operating junction temperature.
 10. For design aid only, not subject to production testing.

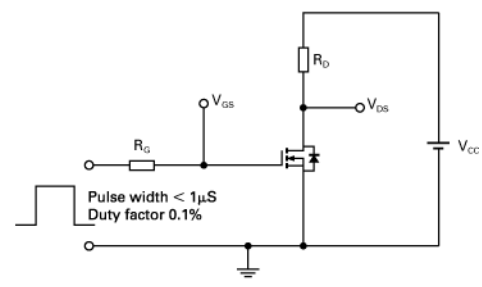
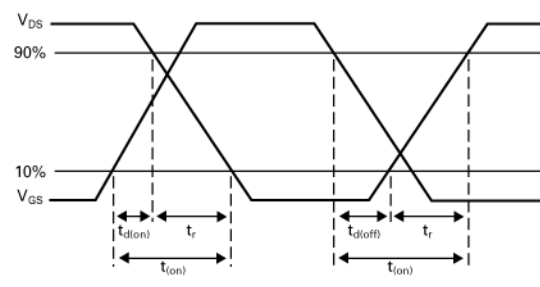
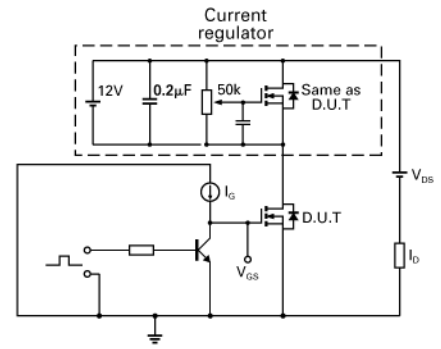
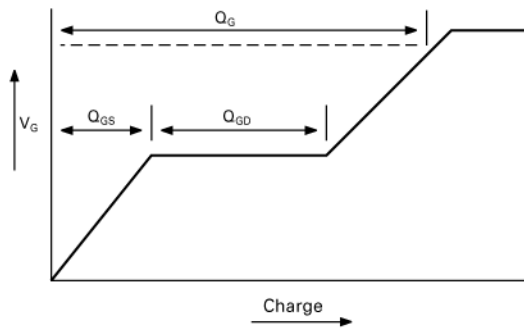
Typical Characteristics



Typical Characteristics (continued)

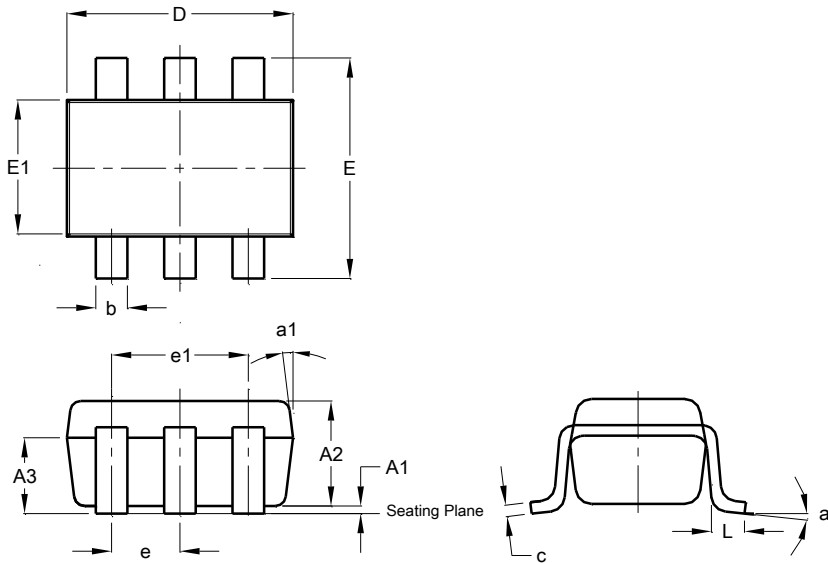


Test Circuits



Package Outline Dimensions

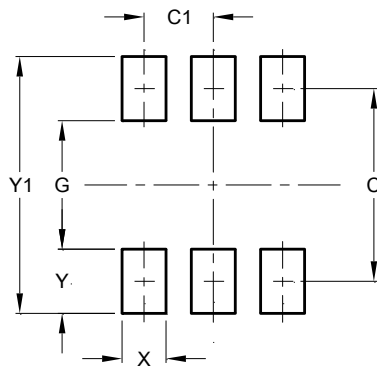
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

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